Claim 2. (Amended) A method as claimed in claim 1, wherein:

heating in the first step comprises a temperature elevating step of elevating the temperature of the substrate from a first temperature Te at which etching of the surface of the substrate by the impurity is started to a second temperature not lower than a temperature at which the single crystal SiC layer is formed, the temperature elevating step being carried out on such a condition that the partial pressure of the raw material is adjusted to a level not lower than 100 times that of the impurity, and

the temperature elevating step being carried out by selecting at least one of a temperature elevating rate and a temperature elevating time within a range such that the density and the size of a defect such as etch pits or dome-like protrusions is suppressed to prevent occurrence of a planar defect on SiC which is deposited on the single crystal SiC layer by the vapor phase growth method or the liquid phase growth method.

Claim 3. (Amended) A method as claimed in claim 1, wherein:

at least one material selected from the group consisting of C_nH_{2n} ($2 \leq n \leq 3$), C_nH_{2n+2} ($1 \leq n \leq 3$), C_nH_{2n-2} ($1 \leq n \leq 3$), CCl_4, CHF_3, and CF_4 is used as the material containing C and used in the in the first step for forming the single crystal SiC layer.

Claim 4. (Amended) A method as claimed in claim 1, wherein:

at least one material selected from the group consisting of SiH_2Cl_2, SiH_4, $SiCl_4$, $SiHCl_3$, Si_2H_6, and Si_2Cl_6 is used as the material containing Si and used in the first step of forming the single crystal SiC layer in addition to the material containing C.

Please add the following new claims:

Claim 11. A method as claimed in claim 1, wherein: the substrate is a Si single crystal substrate.